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(54) Title: METHOD FOR THE PREPARATION OF A MULTI-LAYERED CRYSTALLINE STRUCTURE

FIG. 1A

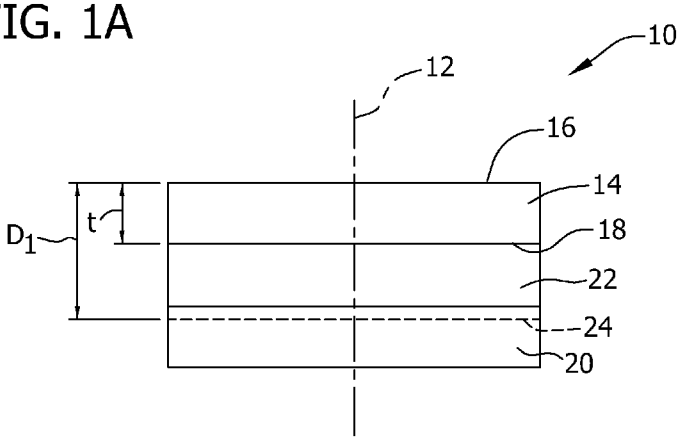
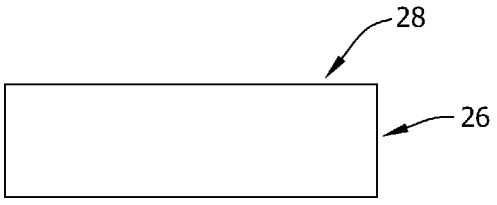


FIG. 1B



(57) Abstract: This invention generally relates to a process for making a multi-layered crystalline structure. The process includes implanting ions into a donor structure, bonding the implanted donor structure to a second structure to form a bonded structure, cleaving the bonded structure, and removing any residual portion of the donor structure from the finished multi-layered crystalline structure.

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